

PSMN8R0-40BS

N-channel 40 V 7.6 m Ω standard level MOSFET in D2PAK

Rev. 2 — 2 March 2012

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC convertors
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$	-	-	40	V	
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	77	Α	
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	86	W	
Static charact	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	6.2	7.6	mΩ	
Dynamic char	acteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 20 \text{ V};$	-	3.8	-	nC	
Q _{G(tot)}	total gate charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	21	-	nC	
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C; } I_D = 77 \text{ A;}$ $V_{sup} \le 40 \text{ V; unclamped; } R_{GS} = 50 \Omega$	-	-	43	mJ	



2. Pinning information

Table 2. Pinning information

		,		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN8R0-40BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	40	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ	-	40	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 ^{\circ}\text{C}; \text{see } \frac{\text{Figure 1}}{}$	-	55	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	77	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$; see Figure 3	-	309	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	86	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drain	diode				
I _S	source current	T _{mb} = 25 °C	-	77	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	309	Α
Avalanche rug	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 77 A; $V_{sup} \le$ 40 V; unclamped; R_{GS} = 50 Ω	-	43	mJ

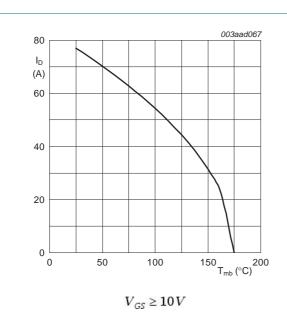


Fig 1. Continuous drain current as a function of mounting base temperature

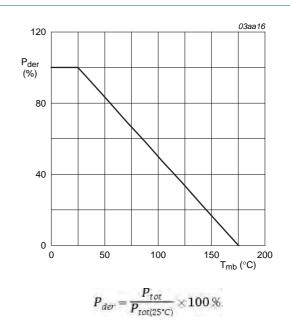
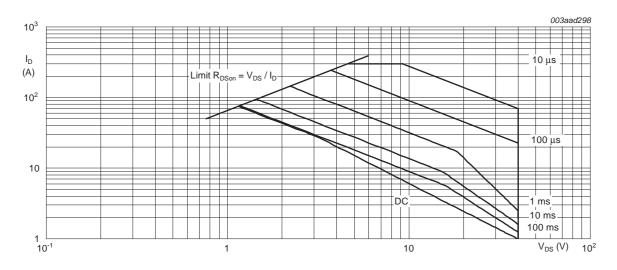


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	1.2	1.74	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on a printed circuit board	-	50	-	K/W

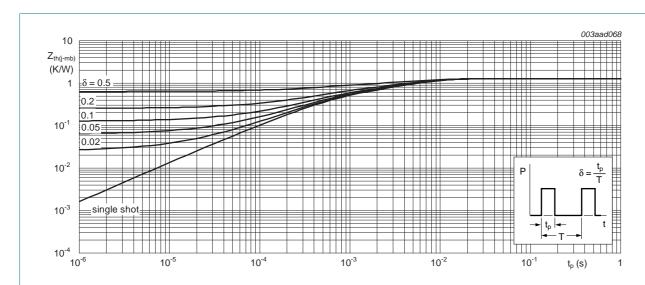


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	4.6	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 10; see Figure 11	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1.5	μΑ
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 125 °C	-	-	30	μΑ
I _{GSS} gate	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R _{DSon} drain-source on-staresistance	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	11	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	6.2	7.6	mΩ
R_{G}	internal gate resistance (AC)	f = 1 MHz	-	1.1	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	Q _{G(tot)} total gate charge	$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	17	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$	-	21	-	nC
Q_{GS}	gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	7.2	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	3.6	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	3.6	-	nC
Q_{GD}	gate-drain charge	$I_D = 25 \text{ A}$; $V_{DS} = 20 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	3.8	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}$; $V_{DS} = 20 \text{ V}$; see <u>Figure 14</u>	-	4.8	-	V
C _{iss}	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1262	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	327	-	pF
C _{rss}	reverse transfer capacitance		-	160	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 12 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 10 \text{ V};$	-	12	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	4.7	-	ns
t _{d(off)}	turn-off delay time		-	21	-	ns
t _f	fall time		-	4.7	-	ns

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 Table 6.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	in diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 50 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}$	-	30	-	ns
Q _r	recovered charge	$I_S = 50 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	18	-	nC

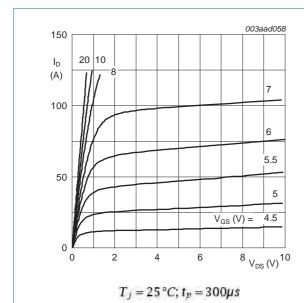


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

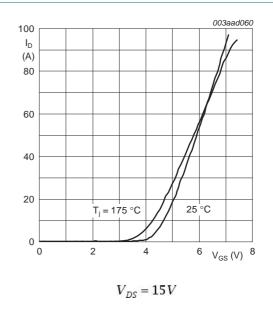


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

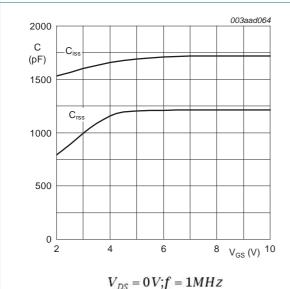
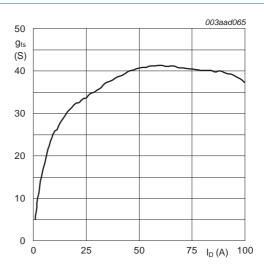


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



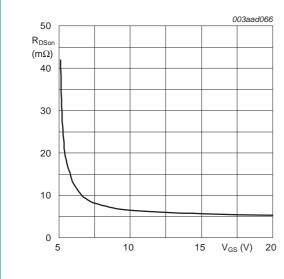
 $T_j = 25 \,^{\circ}C; V_{DS} = 15 V$

Fig 8. Forward transconductance as a function of drain current; typical values

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 $T_j = 25\,^{\circ}C; I_D = 25A$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

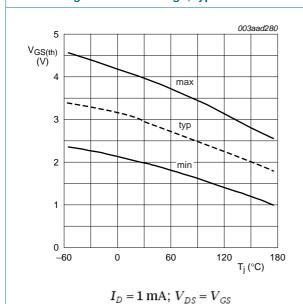
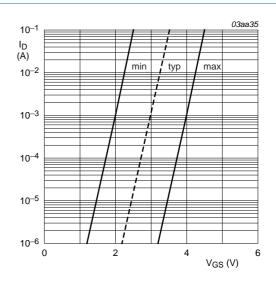


Fig 11. Gate-source threshold voltage as a function of junction temperature



$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

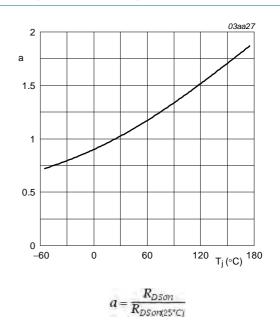
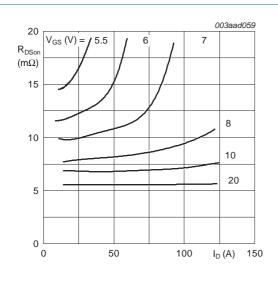


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



 $T_j = 25 \,^{\circ}C; t_p = 300 \mu s$

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

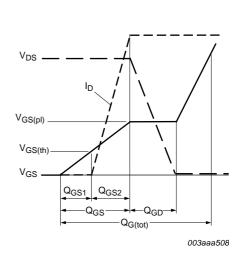
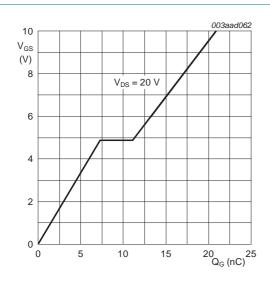
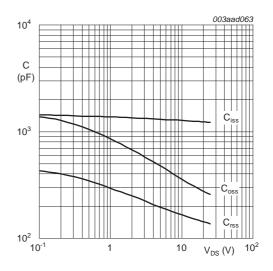


Fig 14. Gate charge waveform definitions



 $T_j = 25\,^{\circ}C; I_D = 25A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$$V_{GS} = 0V; f = 1MHz$$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

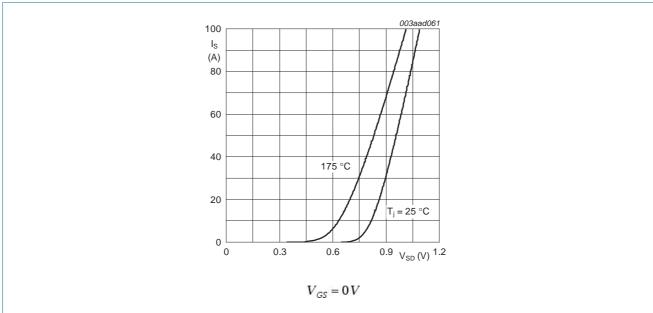


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

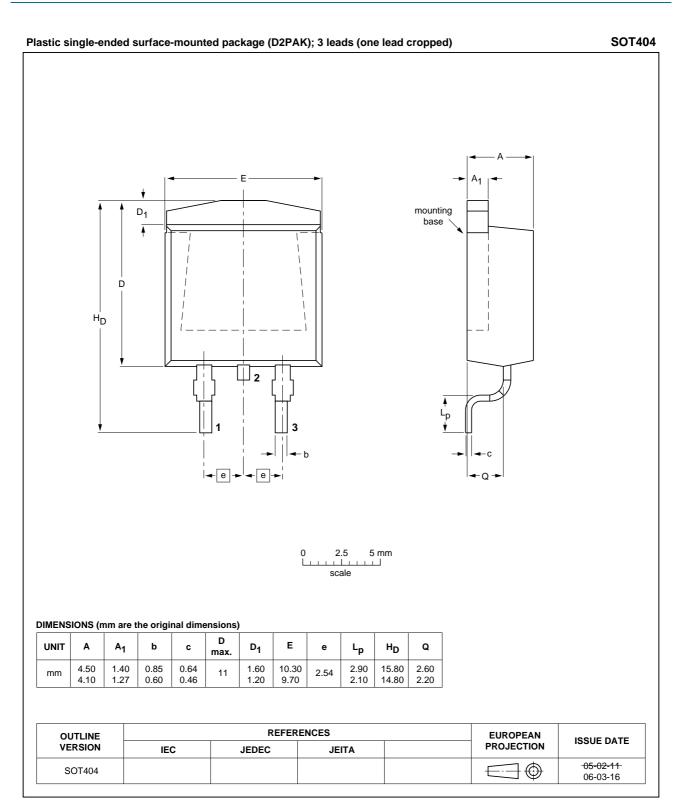


Fig 18. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN8R0-40BS v.2	20120302	Product data sheet	-	PSMN8R0-40BS v.1
Modifications:	Status changed frVarious changes	om objective to product. to content.		
PSMN8R0-40BS v.1	20111021	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Product data sheet

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